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2N6098

SILICON NPN - POWER TRANSISTOR

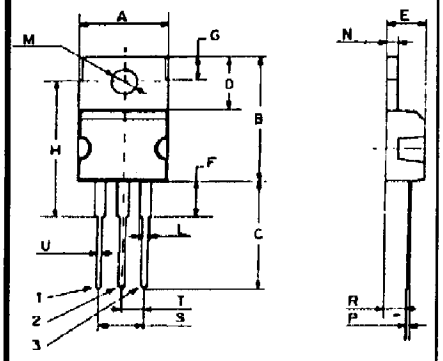
DESCRIPTION:

The **2N6098** is an NPN Silicon Power Transistor for General Purpose Switching and Amplifier Applications.

MAXIMUM RATINGS

I_C	10 A
I_B	4.0 A
V_{CE}	60 V
P_{DISS}	75 W @ T_C = 25 °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.67 °C/W

PACKAGE STYLE TO-220



pin 1: Base - pin 2: Collector - pin 3: Emitter

	DIMENSIONS			
	mm		inches	
	min	max	min	max
A	10	10.4	0.393	0.409
B	15.2	15.9	0.598	0.626
C	12.7	13.7	0.500	0.539
D	6.2	6.6	0.244	0.260
E	4.4	4.6	0.173	0.181
F	3.5	5.5	0.137	0.216
G	2.65	2.95	0.104	0.116
H	17.6 typ.		0.692 typ.	
L	1.14	1.7	0.044	0.067
M	3.75	3.85	0.147	0.151
N	1.23	1.32	0.048	0.051
P	0.41	0.64	0.016	0.025
R	2.4	2.72	0.094	0.107
S	4.95	5.15	0.194	0.203
T	2.4	2.7	0.094	0.106
U	0.61	0.94	0.024	0.037

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{CEO}	I_C = 200 mA	60			V
V_{CER}	I_C = 200 mA R_{BE} = 100 Ω	65			V
I_{CEO}	V_{CE} = 50 V			2.0	mA
I_{CEX}	V_{CE} = 75 V V_{BE} = -1.5 V T_C = 25 °C T_C = 150 °C			2.0 10	mA
I_{EBO}	V_{EB} = 8.0 V			1.0	mA
h_{FE}	V_{CE} = 4.0 V I_C = 4.0 A I_C = 10 A	20 5.0		80	---
$V_{CE(SAT)}$	I_C = 10 A I_B = 2.0 A			2.5	V
$V_{BE(ON)}$	V_{CE} = 4.0 V I_C = 4.0 A			1.7	V
h_{fe}	V_{CE} =4.0 V I_C = 0.5 A f = 1.0 KHz	15			---
f_t	V_{CE} = 4.0 V I_C = 0.5 A f = 0.1 MHz	8.0		28	---